

## **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

1. (Currently Amended) A method of growing a gallium nitride single crystal using a flux comprising at least sodium metal, said method comprising:  
  
growing said gallium nitride single crystal in an atmosphere comprising nitrogen gas and having a total pressure of 300 atms to 1200 atms and at a temperature of 900°C to 1200°C, said atmosphere having a nitrogen pressure of 120 atms to 600 atms, wherein the gallium nitride single crystal is grown at a rate of at least 25  $\mu\text{m/hr}$ .
- 2-3. (Cancelled).
4. (Previously Presented) The method of claim 1, wherein said crystal is grown at a temperature of 950°C to 1200°C.
5. (Previously Presented) The method of claim 1, further comprising the step of elevating a crucible containing said flux until a seed crystal contacts said flux.
6. (Previously Presented) The method of claim 1, wherein said gallium nitride single crystal is grown using a system for hot isostatic pressing.

7-12. (Cancelled).

13. (Previously Presented) The method of claim 5, further comprising the step of driving the crucible downward after a predetermined amount of time, to separate the seed crystal from said flux.

14. (Previously Presented) The method of claim 1, wherein the gallium nitride single crystal is grown on a seed crystal having a lateral dimension and the gallium nitride single crystal has the same lateral dimension.